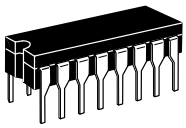
MC14015B

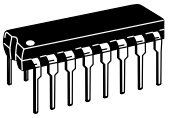
Dual 4-Bit Static Shift Register

The MC14015B dual 4–bit static shift register is constructed with MOS P–channel and N–channel enhancement mode devices in a single monolithic structure. It consists of two identical, independent 4–state serial–input/parallel–output registers. Each register has independent Clock and Reset inputs with a single serial Data input. The register states are type D master–slave flip–flops. Data is shifted from one stage to the next during the positive–going clock transition. Each register can be cleared when a high level is applied on the Reset line. These complementary MOS shift registers find primary use in buffer storage and serial–to–parallel conversion where low power dissipation and/or noise immunity is desired.

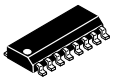
- Diode Protection on All Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Logic Edge–Clocked Flip–Flop Design — Logic state is retained indefinitely with clock level either high or low; information is transferred to the output only on the positive going edge of the clock pulse.
- Capable of Driving Two Low–power TTL Loads or One Low–power Schottky TTL Load Over the Rated Temperature Range.



L SUFFIX
CERAMIC
CASE 620



P SUFFIX
PLASTIC
CASE 648



D SUFFIX
SOIC
CASE 751B

ORDERING INFORMATION

MC14XXXBCP	Plastic
MC14XXXBCL	Ceramic
MC14XXXBD	SOIC

T_A = – 55° to 125°C for all packages.

MAXIMUM RATINGS* (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage	– 0.5 to + 18.0	V
V_{in}, V_{out}	Input or Output Voltage (DC or Transient)	– 0.5 to V_{DD} + 0.5	V
I_{in}, I_{out}	Input or Output Current (DC or Transient), per Pin	± 10	mA
P_D	Power Dissipation, per Package†	500	mW
T_{stg}	Storage Temperature	– 65 to + 150	°C
T_L	Lead Temperature (8–Second Soldering)	260	°C

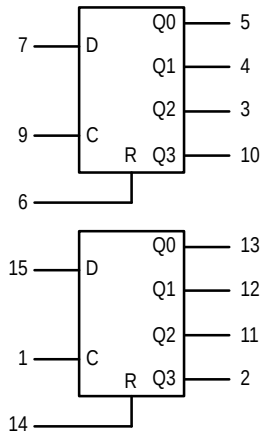
* Maximum Ratings are those values beyond which damage to the device may occur.
†Temperature Derating:
Plastic “P and D/DW” Packages: – 7.0 mW/°C From 65°C To 125°C
Ceramic “L” Packages: – 12 mW/°C From 100°C To 125°C

TRUTH TABLE

C	D	R	Q0	Q_n
↗	0	0	0	Q_{n-1}
↗	1	0	1	Q_{n-1}
↘	X	0	No Change	No Change
X	X	1	0	0

X = Don’t Care
Q_n = Q0, Q1, Q2, or Q3, as applicable.
Q_{n-1} = Output of prior stage.

BLOCK DIAGRAM



V_{DD} = PIN 16
V_{SS} = PIN 8

REV 3
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ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	– 55°C Min	– 55°C Max	25°C Min	25°C Typ #	25°C Max	125°C Min	125°C Max	Unit
Output Voltage "0" Level V_{in} = V_{DD} or 0	V_{OL}	5.0 10 15	— — —	0.05 0.05 0.05	— — —	0 0 0	0.05 0.05 0.05	— — —	0.05 0.05 0.05	Vdc
V_{in} = 0 or V_{DD} "1" Level	V_{OH}	5.0 10 15	4.95 9.95 14.95	— — —	4.95 9.95 14.95	5.0 10 15	— — —	4.95 9.95 14.95	— — —	Vdc
Input Voltage "0" Level	V_{IL}									Vdc
(V_O = 4.5 or .05 Vdc)		5.0	—	1.5	—	2.25	1.5	—	1.5	
(V_O = 9.0 or 1.0 Vdc)		10	—	3.0	—	4.50	3.0	—	3.0	
(V_O = 13.5 or 1.5 Vdc)		15	—	4.0	—	6.75	4.0	—	4.0	
(V_O = 0.5 or 4.5 Vdc) "1" Level	V_{IH}	5.0	3.5	—	3.5	2.75	—	3.5	—	Vdc
(V_O = 1.0 or 9.0 Vdc)		10	7.0	—	7.0	5.50	—	7.0	—	
(V_O = 1.5 or 13.5 Vdc)		15	11	—	11	8.25	—	11	—	
Output Drive Current	I_{OH}									mAdc
(V_{OH} = 2.5 Vdc) Source		5.0	– 3.0	—	– 2.4	– 4.2	—	– 1.7	—	
(V_{OH} = 4.6 Vdc)		5.0	– 0.64	—	– 0.51	– 0.88	—	– 0.36	—	
(V_{OH} = 9.5 Vdc)		10	– 1.6	—	– 1.3	– 2.25	—	– 0.9	—	
(V_{OH} = 13.5 Vdc)		15	– 4.2	—	– 3.4	– 8.8	—	– 2.4	—	
(V_{OL} = 0.4 Vdc) Sink	I_{OL}	5.0	0.64	—	0.51	0.88	—	0.36	—	mAdc
(V_{OL} = 0.5 Vdc)		10	1.6	—	1.3	2.25	—	0.9	—	
(V_{OL} = 1.5 Vdc)		15	4.2	—	3.4	8.8	—	2.4	—	
Input Current	I_{in}	15	—	± 0.1	—	±0.00001	± 0.1	—	± 1.0	µAdc
Input Capacitance (V_{in} = 0)	C_{in}	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current (Per Package)	I_{DD}	5.0 10 15	— — —	5.0 10 20	— — —	0.005 0.010 0.015	5.0 10 20	— — —	150 300 600	µAdc
Total Supply Current**† (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0 10 15	I_T = (1.2 µA/kHz)f + I_{DD} I_T = (2.4 µA/kHz)f + I_{DD} I_T = (3.6 µA/kHz)f + I_{DD}							µAdc

#Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

**The formulas given are for the typical characteristics only at 25°C.

†To calculate total supply current at loads other than 50 pF:

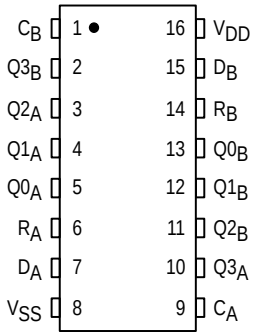
$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

where: I_T is in µA (per package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency, and k = 0.002.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

PIN ASSIGNMENT



SWITCHING CHARACTERISTICS* (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD}	Min	Typ #	Max	Unit
Output Rise and Fall Time	t_{TLH},					ns
t_{TLH}, t_{THL} = (1.5 ns/pF) C_L + 25 ns	t_{THL}	5.0	—	100	200	
t_{TLH}, t_{THL} = (0.75 ns/pF) C_L + 12.5 ns		10	—	50	100	
t_{TLH}, t_{THL} = (0.55 ns/pF) C_L + 9.5 ns		15	—	40	80	
Propagation Delay Time	t_{PLH},					ns
Clock, Data to Q	t_{PHL}					
t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 225 ns		5.0	—	310	750	
t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 92 ns		10	—	125	250	
t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 65 ns		15	—	90	170	
Reset to Q						
t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 375 ns		5.0	—	460	750	
t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 147 ns		10	—	180	250	
t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 95 ns		15	—	120	170	
Clock Pulse Width	t_{WH}	5.0	400	185	—	ns
		10	175	85	—	
		15	135	55	—	
Clock Pulse Frequency	f_{cl}	5.0	—	2.0	1.5	MHz
		10	—	6.0	3.0	
		15	—	7.5	3.75	
Clock Pulse Rise and Fall Times	t_{TLH}, t_{THL}	5.0	—	—	15	µs
		10	—	—	5	
		15	—	—	4	
Reset Pulse Width	t_{WH}	5.0	400	200	—	ns
		10	160	80	—	
		15	120	60	—	
Setup Time	t_{su}	5.0	350	100	—	ns
		10	100	50	—	
		15	75	40	—	

* The formulas given are for typical characteristics only at 25°C.
#Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.

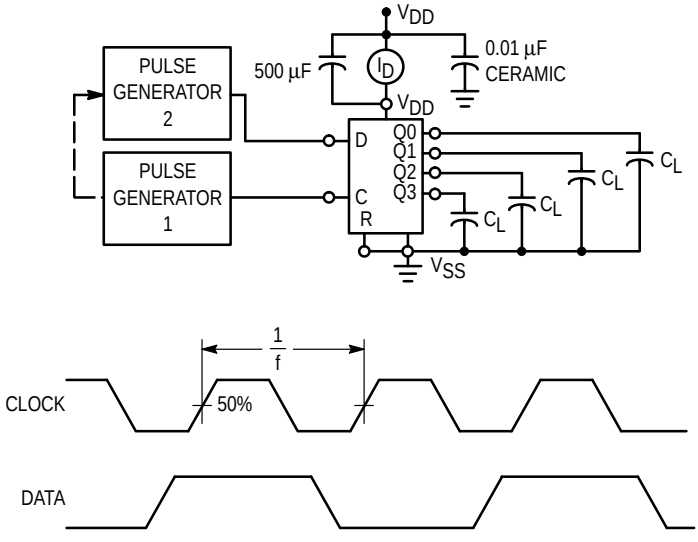


Figure 1. Power Dissipation Test Circuit and Waveform

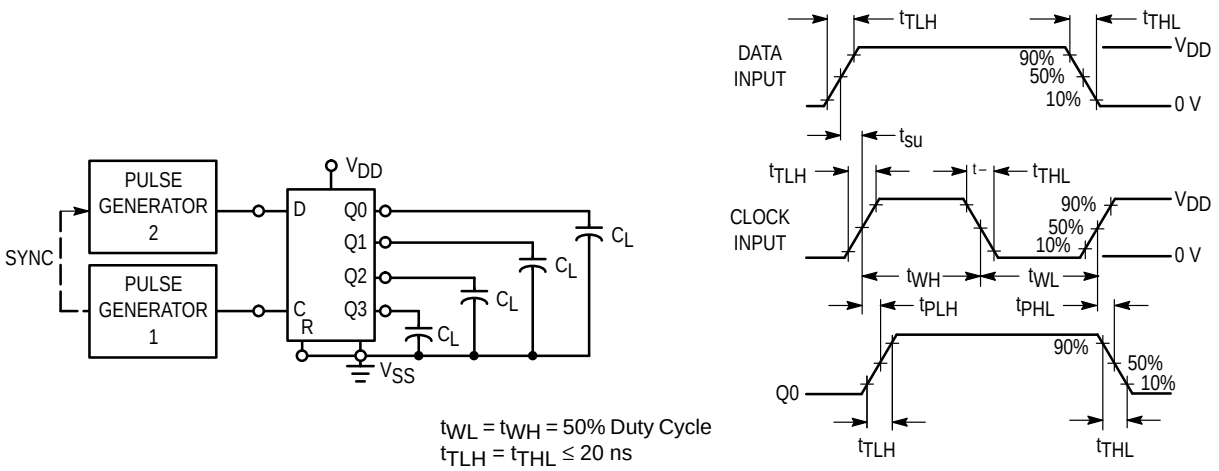


Figure 2. Switching Test Circuit and Waveforms

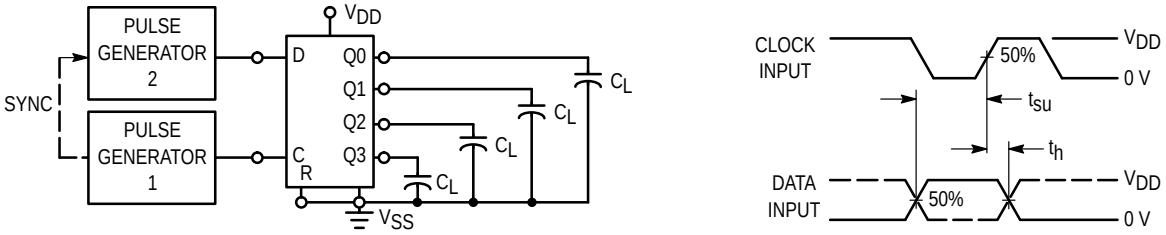
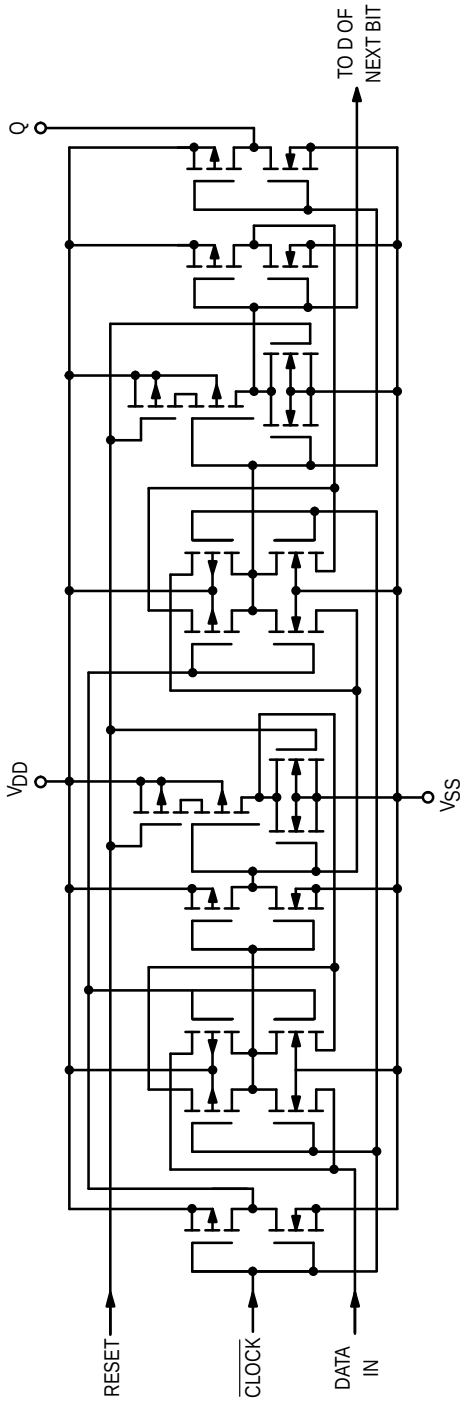


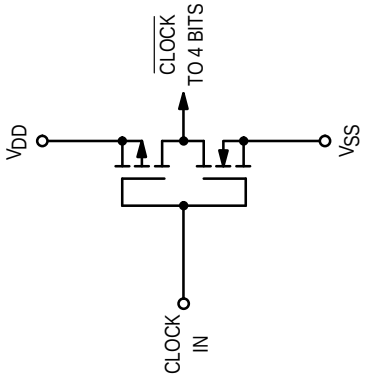
Figure 3. Setup and Hold Time Test Circuit and Waveforms

CIRCUIT SCHEMATICS

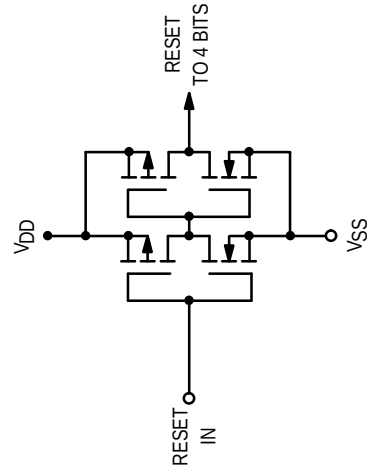
SINGLE BIT



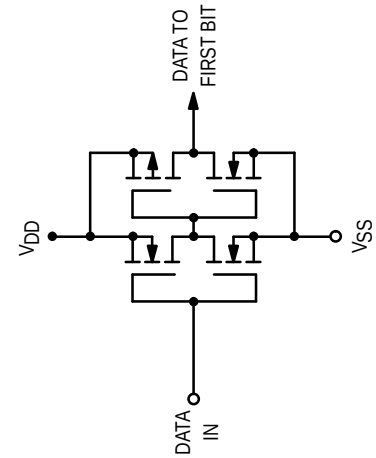
CLOCK INPUT BUFFER



RESET INPUT BUFFER

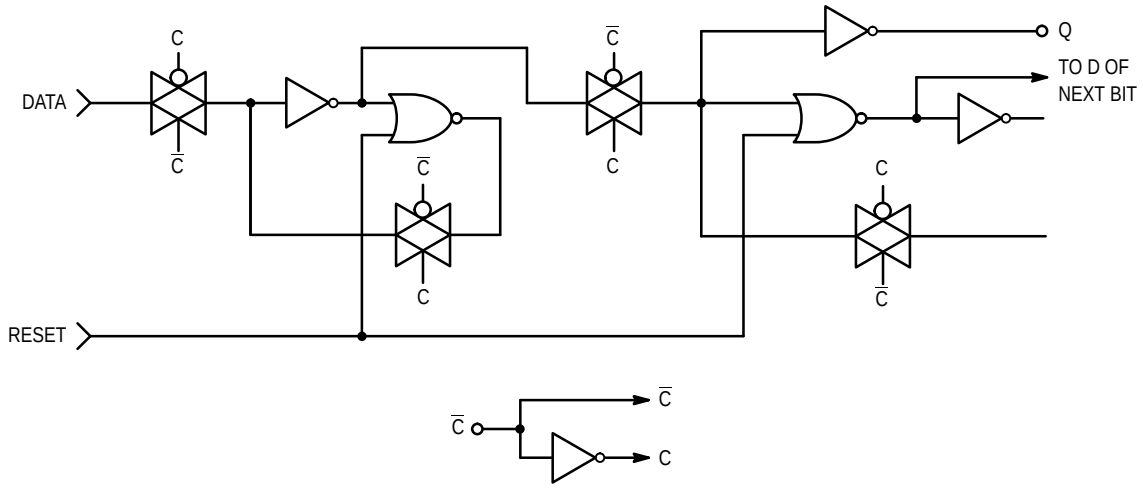


DATA INPUT BUFFER

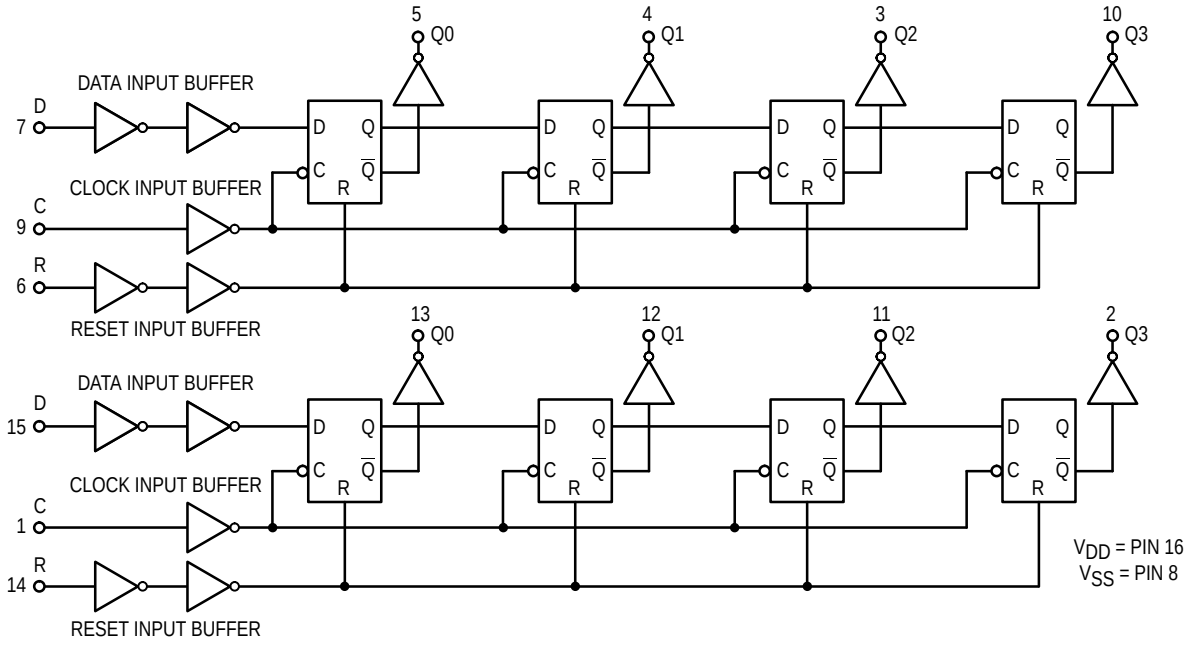


LOGIC DIAGRAMS

SINGLE BIT

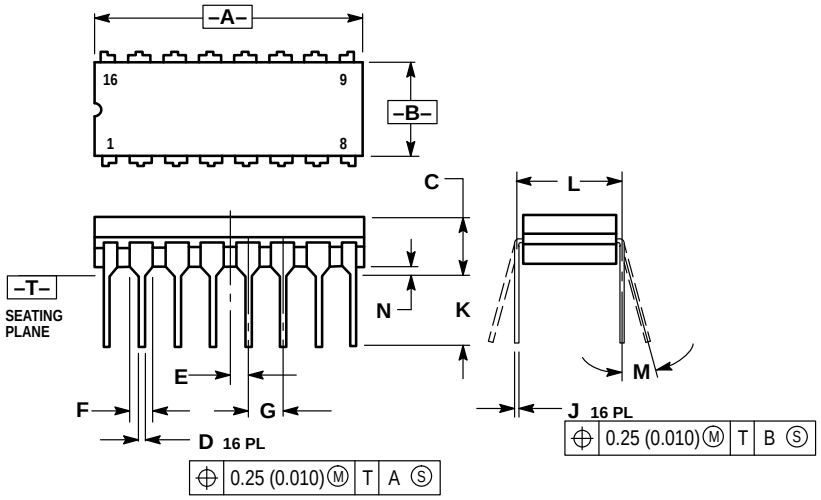


COMPLETE DEVICE



OUTLINE DIMENSIONS

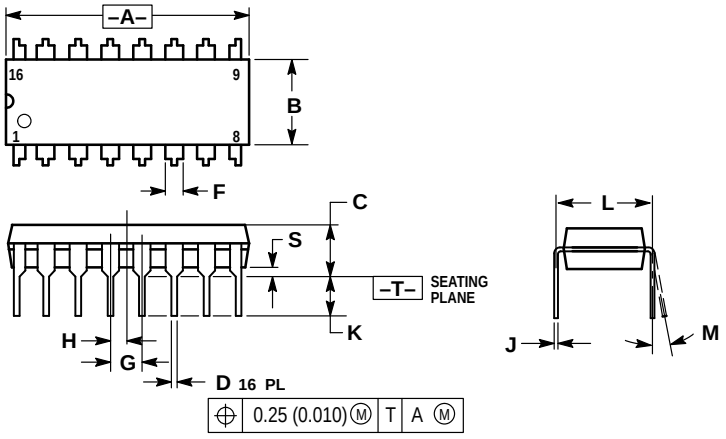
L SUFFIX
CERAMIC DIP PACKAGE
CASE 620–10
ISSUE V



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.750	0.785	19.05	19.93
B	0.240	0.295	6.10	7.49
C	—	0.200	—	5.08
D	0.015	0.020	0.39	0.50
E	0.050 BSC		1.27 BSC	
F	0.055	0.065	1.40	1.65
G	0.100 BSC		2.54 BSC	
H	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300 BSC		7.62 BSC	
M	0 °	15 °	0 °	15 °
N	0.020	0.040	0.51	1.01

P SUFFIX
PLASTIC DIP PACKAGE
CASE 648–08
ISSUE R

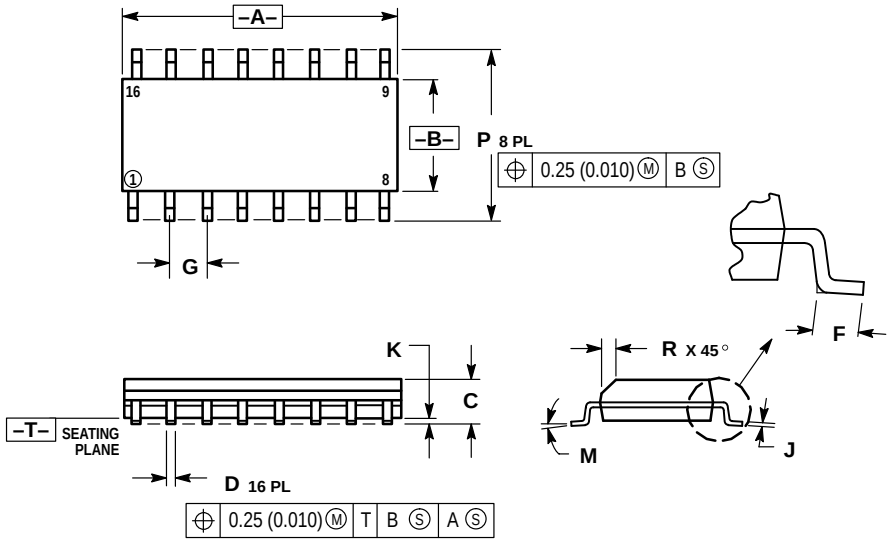


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0 °	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01

OUTLINE DIMENSIONS

D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751B–05
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

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